MRF313

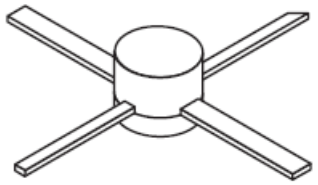
The RF Line NPN Silicon High-Frequency Transistor
1.0W, 400MHz, 28V

Rev. V1

Designed for wideband amplifier, driver or oscillator applications in military, mobile, and aircraft radio.

- Specified 28 V, 400 MHz characteristics —
  Output power = 1.0 W
  Power gain = 15 dB min.
  Efficiency = 45% typ.
- Emitter ballast and low current density for improved MTBF
- Common emitter for improved stability

Product Image



CASE 305A–01, STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	30	Vdc
Collector–Base Voltage	V_{CBO}	40	Vdc
Emitter–Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	150	mAdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	6.1 35	Watts mW/°C
Storage Temperature Range	T_{stg}	–65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	28.5	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

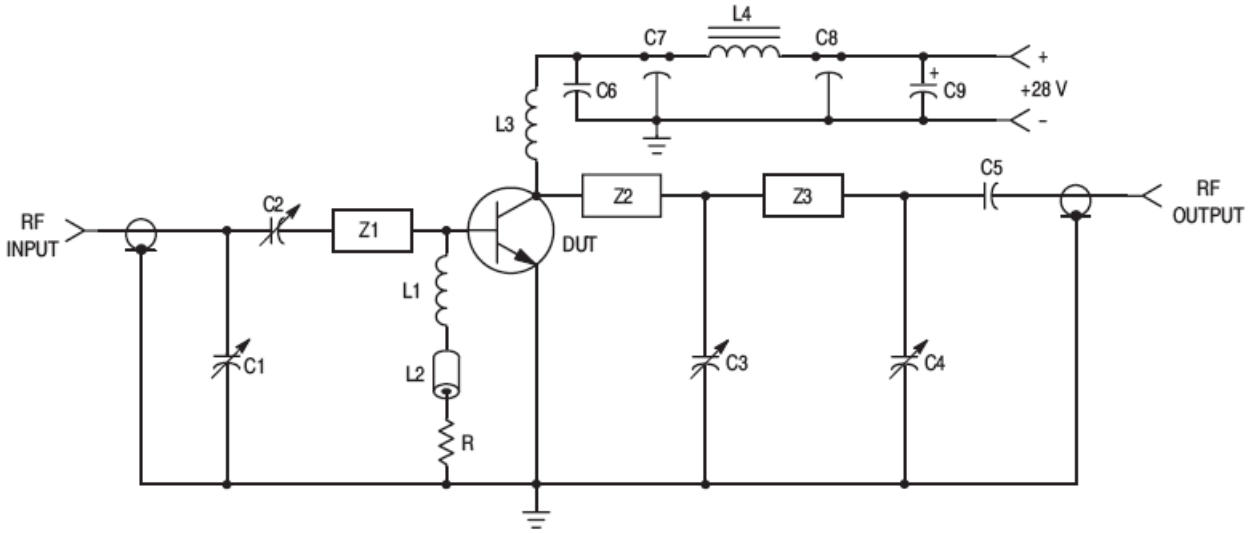
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector–Emitter Breakdown Voltage (I_C = 5.0 mAdc, V_{BE} = 0)	$V_{(BR)CES}$	35	—	—	Vdc
Collector–Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	35	—	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 1.0 mAdc, I_C = 0)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current (V_{CE} = 20 Vdc, I_B = 0)	I_{CEO}	—	—	1.0	mAdc

(continued)

ELECTRICAL CHARACTERISTICS — continued (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 mAdc, V_{CE} = 10 Vdc)	h_{FE}	20	60	150	—
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I_C = 100 mAdc, V_{CE} = 20 Vdc, f = 200 MHz)	f_T	—	2.5	—	GHz
Output Capacitance (V_{CB} = 28 Vdc, I_E = 0, f = 1.0 MHz)	C_{ob}	—	3.5	5.0	pF
FUNCTIONAL TESTS					
Common–Emitter Amplifier Power Gain (1) (V_{CC} = 28 Vdc, P_{out} = 1.0 W, f = 400 MHz)	G_{pe}	15	16	—	dB
Collector Efficiency (V_{CC} = 28 Vdc, P_{out} = 1.0 W, f = 400 MHz)	η	—	45	—	%
Series Equivalent Input Impedance (V_{CC} = 28 Vdc, P_{out} = 1.0 W, f = 400 MHz)	Z_{in}	—	6.4 – j4.8	—	Ohms
Series Equivalent Output Impedance (V_{CC} = 28 Vdc, P_{out} = 1.0 W, f = 400 MHz)	Z_{out}	—	75 – j45	—	Ohms

NOTE:
1. Class C



C1, C2, C4 — 1.0–20 pF JOHANSON 9063
C3 — 1.0–10 pF JOHANSON
C5 — 150 pF Chip
C6 — 0.1 µF
C7, C8 — 680 pF Feedthru
C9 — 1.0 µF TANTALUM

L1, L3 — 5 Turns, AWG #20, 1/4″ I.D.
L2 — Ferrite Bead, FERROXCUBE
No. 56–590–65/4B
L4 — FERROXCUBE VK200–20/4B
Input/Output Connectors — Type N
Board — Glass Teflon, ε = 2.56, t = 0.062″

R — 4.7 Ohms, 1/4 W
Z1 — 2.0″ x 0.1″ MICROSTRIP LINE
Z2, Z3 — 2.6″ x 0.1″ MICROSTRIP LINE

Figure 1. 400 MHz Power Gain Test Circuit

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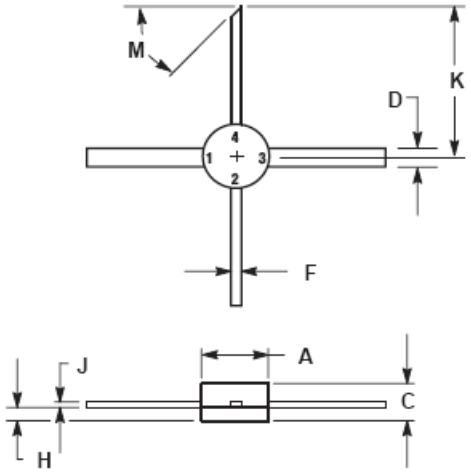
PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.200	0.220	5.08	5.59
C	0.095	0.130	2.41	3.30
D	0.055	0.065	1.40	1.65
F	0.025	0.035	0.64	0.89
H	0.040	0.050	1.02	1.27
J	0.003	0.007	0.08	0.18
K	0.435	---	11.05	---
M	45 °REF		45 °REF	

STYLE 1:
PIN 1. EMITTER
2. BASE
3. EMITTER
4. COLLECTOR

CASE 305A–01
ISSUE A